
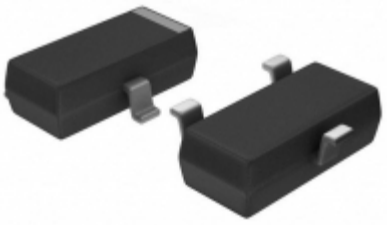
	<p><b>SI2319DS-T1-GE3</b></p>
	<p><b>Hersteller-Teilenummer:</b> SI2319DS-T1-GE3</p> <p><b>Hersteller / Marke:</b> Vishay / Siliconix</p> <p><b>Teil der Beschreibung:</b> MOSFET P-CH 40V 2.3A SOT23-3</p> <p><b>Datenblätter:</b>  <a href="#">SI2319DS-T1-GE3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 84929 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2319DS-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 40V 2.3A SOT23-3
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	84929 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	750mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	40V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	2.3A (Ta)
Rds On (Max) @ Id, Vgs	82 mOhm @ 3A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	17nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	470pF @ 20V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)

SI2319DS-T1-GE3 ist neu im Original, Suche SI2319DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2319DS-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2319DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p><b>SI2320DS-T1-GE3</b> VISHAY SI2320DS-T1-GE3 VISHAY</p>	 <p><b>SI2320DS-T1-GE3 @@</b> 69K SI2320DS-T1-GE3 @@ 69K</p>	 <p><b>SI2320DS</b> VISHAY SI2320DS VISHAY</p>	 <p><b>SI2319DS</b> 89K SI2319DS 89K</p>
 <p><b>SI2320DS-T1</b> VISHAY SI2320DS-T1 VISHAY</p>	 <p><b>SI2319DS-T1-E3</b> Vishay / Siliconix MOSFET P-CH 40V 2.3A SOT23-3</p>	 <p><b>SI2319DDS-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET P-CHAN 40V</p>	 <p><b>SI2320DS-T1-E3</b> VISHAY SI2320DS-T1-E3 VISHAY</p>

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|--|--|--|---|--|
|  SI2316DS-T1-GE3  |  SI2316DS-T1-GE3  |  SI2317DS         |  SI2317DS-T1-E3   |  SI2318ADS-T1-GE3 |
|  SI2318BDS-T1-E3  |  SI2318BDS-T1-GE3 |  SI2318CDS-T1-E3  |  SI2318CDS-T1-GE3 |  SI2318CDS-T1-GE3 |
|  SI2318DS         |  SI2318DS-T1-E3   |  SI2318DS-T1-E3   |  SI2318DS-T1-GE3  |  SI2318DS-T1-GE3  |
|  SI2319ADS-T1-GE3 |  SI2319C95TF      |  SI2319CDS-T1-E3  |  SI2319CDS-T1-GE3 |  SI2319CDS-T1-GE3 |
|  SI2319DDS-T1-GE3 |  SI2319DS         |  SI2319DS-T1-E3   |  SI2319DS-T1-E3   |  SI2319DS-T1-GE3  |
|  SI2320DS         |  SI2320DS-T1-E3   |  SI2320DS-T1-GE3  |  SI2321DS-T1-E3   |  SI2321DS-T1-E3   |
|  SI2321DS-T1-GE3  |  SI2321DS-T1-GE3  |  SI2323CDS-T1     |  SI2323CDS-T1-E3  |  SI2323CDS-T1-GE3 |
|  SI2323CDS-T1-GE3 |  SI2323DDS-T1-E3  |  SI2323DDS-T1-GE3 |  SI2323DDS-T1-GE3 |  SI2323DS         |
|  SI2323DS-T1-E3   |  SI2323DS-T1-E3   |  SI2323DS-T1-GE3  |  SI2323DS-T1-GE3  |  SI2324DS-T1-E3   |
|  SI2324DS-T1-GE3  |  SI2324DS-T1-GE3  |  SI2325DS-T1-E3   |  SI2325DS-T1-E3   |  SI2325DS-T1-GE3  |

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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